

VDS	RDS(on)	ID@25℃
1700V	1000mΩ	5A

# **Applications:**

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- EV Charging
- Motor Drives

#### Features:

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness

#### **Benefits:**

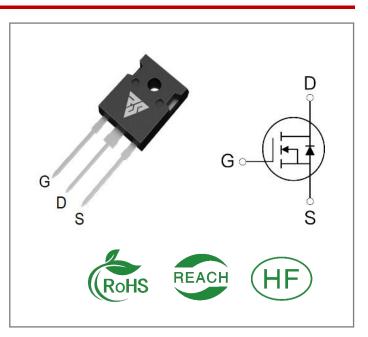
- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

# **Ordering Information**

Part Number	Package	Marking	Packing	Qty.
RSM1701K0W	TO-247-3	RSM1701K0W	Tube	30 PCS

# Maximum Ratings (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
VDSmax	Drain - Source Voltage	1700	V	VGS=0V,ID =100µA	
VGSmax	Gate - Source Voltage	-10/+2 5	V Absolute maximum values		
VGSop	Gate - Source Voltage	-5/+20	V	Recommended operational values	
ID	Continuous Drain Current	5 3.5	А	VGS=20V, TC =25℃ VGS=20V, TC =100℃	
ID(pulse)	Pulsed Drain Current	6	A		
PD	Power Dissipation	69	W	TC =25℃, TJ =150℃	
TL	Solder Temperature	260	°C		
TJ, Tstg	Operating Junction and StorageTemperature	-40 to + 150	°C		





# **Electrical Characteristics** (TJ= 25°C unless otherwise specified)

Symbol	Parameter	Min.	Тур.	Max	Unit	Test Conditions	Note
V(BR)D SS	Drain-Source Breakdown Voltage	1700			V	VGS=0V,ID =100µA	
	Gate Threshold	2.5	3.0	4.5	V	VGS= VDS, IDS=1mA,TC =25℃	
VGS(th)	Voltage		2.2		V	VGS= VDS, IDS=1mA,TC =150℃	
IDSS	Zero Gate Voltage Drain Current		1	100	μA	VDS= 1700V, VGS=0V	
IGSS	Gate-Source Leakage Current			250	nA	VGS=25V, VDS= 0V	
RDS(on)	Drain-Source on-state		1000	1300	mΩ	VGS=20V, ID =2A, TC =25℃	
KD3(0H)	Resistance		1500			<b>VGS=20V, ID =2A, TC =150</b> ℃	
Ciss	Input Capacitance		186				
Coss	Output Capacitance		12		pF	VGS=0V, VDS=1000 V, f=1MHz, VAC=25 mV	
Crss	Reverse Transfer Capacitance		1.6				
EON	Turn-On Switching Energy		48		μJ	VDS =1200V, VGS =-5/20V,ID = 2A,	
EOFF	Turn-Off Energy		18		μ	$RG(ext) = 2.5\Omega, L = 1500\mu H$	
td(on)	Turn-On Delay Time		5.2				
tr	Rise Time		9.4			VDS =1200V, VGS =-5/20 V	
td(off)	Turn-Off Delay Time		13.2		ns	ID = 2A, RG(ext) =2. 5 Ω , RL =600Ω	
tf	Fall Time		22				
RG(int)	Internal Gate Resistance		22		Ω	f=1 MHz, VAC=25mV	
Qgs	Gate to Source Charge		5.2		nC		
Qgd	Gate to Drain Charge		7.3		nC	VDS=1200V, VGS=-5/20V ID =2A	
Qg	Total Gate Charge		21.8				



# **Reverse Diode Characteristics** (TJ= $25^{\circ}$ C unless otherwise specified)

Symbol	Parameter	Тур.	Max	Unit	Test Conditions	Not e
VSD	Diode Forward Voltage	4.2		V	VGS=-5V, ISD = 1 A, TJ = 25℃	
V3D	Diode Forward Voltage	3.9		V	VGS=-5V, ISD= 1 A, TJ= 150℃	
IS	Continuous Diode Forward Current		4	А	<b>VGS=-5V,TC= 25</b> ℃	
trr	Reverse Recovery time	25		ns		
Qrr	Reverse Recovery Charge	15		nC	ISD= 2 A, VR = 1200V	
Irrm	Peak Reverse Recovery Current	2.8		А		

#### **Thermal Characteristics** (TJ= $25^{\circ}$ C unless otherwise specified)

Symbol	Parameter	Тур.	Unit	Test Conditions	Not e
RθJC	Thermal Resistance from Junction to Case	1.8	°C/W		
RθJA	Thermal Resistance From Junction to Ambient	40	C/VV		



# **Typical Feature Curve**

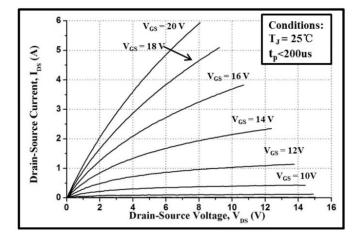


Figure 1. Typical Output Characteristics T<sub>J</sub>= 25°C

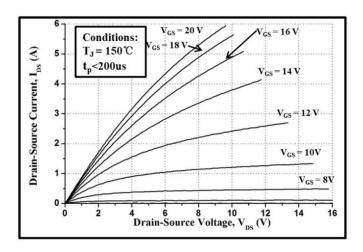


Figure 3. Typical Output Characteristics T<sub>J</sub>=150°C

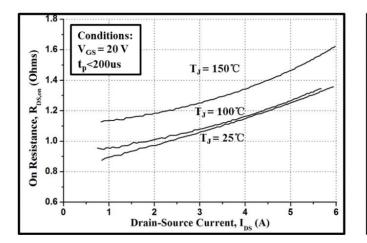


Figure 5. On-Resistance vs. Drain Current

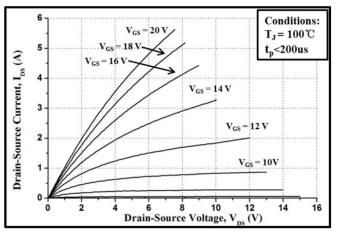


Figure 2. Typical Output Characteristics T<sub>J</sub>= 100°C

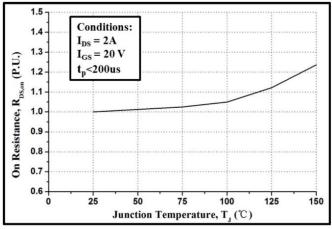
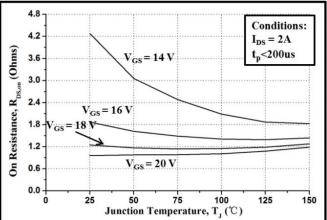
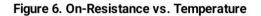
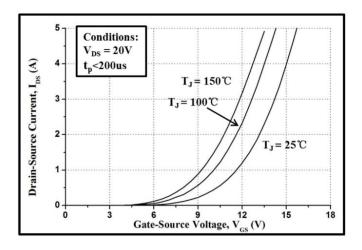


Figure 4. Normalized On-Resistance vs. Temperature









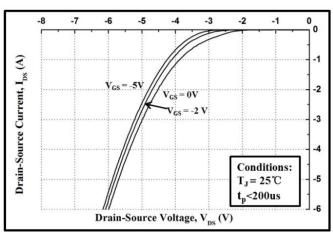
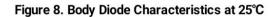


Figure 7. Typical Transfer Characteristics



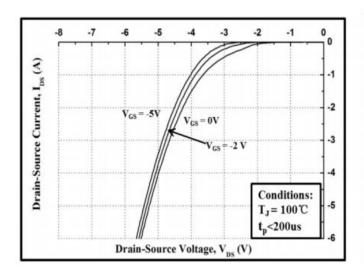


Figure 9. Body Diode Characteristics at 100°C

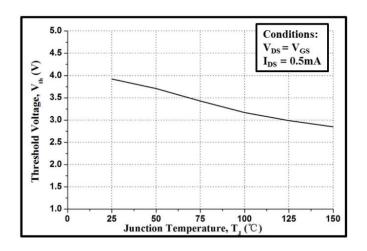


Figure 11. Gate Threshold Voltage vs. Temperature

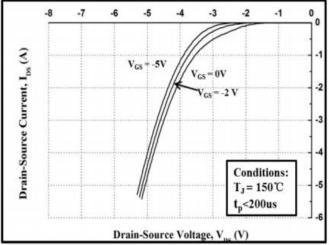


Figure 10. Body Diode Characteristics at 150°C

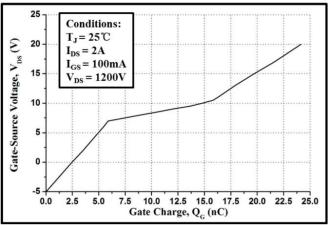
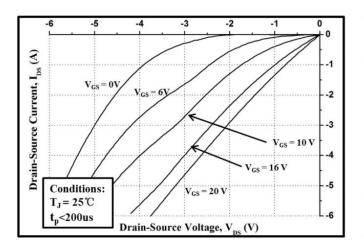


Figure 12. Gate Charge Characteristic







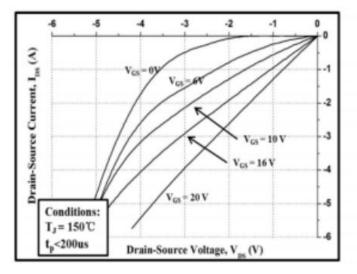


Figure 15. 3rd Quadrant Characteristics at 150°C

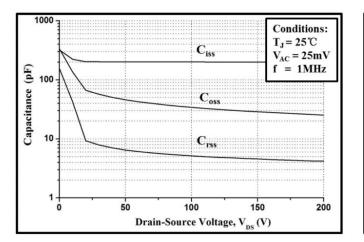


Figure 17. Capactances vs. Drain-Source Voltage

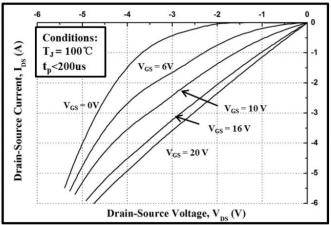


Figure 14. 3rd Quadrant Characteristics at 100°C

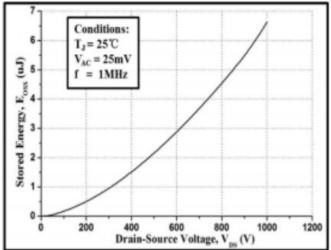


Figure 16. Output Capacitor Stored Energy

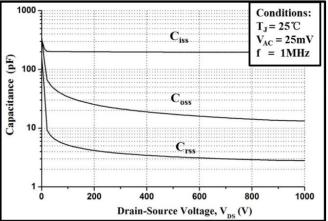


Figure 18. Capactances vs. Drain-Source Voltage

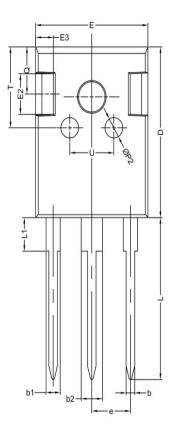


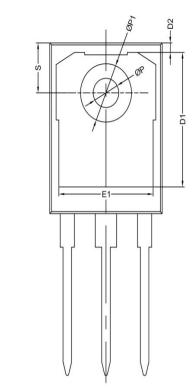
# Package outline drawing(TO-247-3 Unit: mm)

A

A2

A1-





		机械尺寸/mn	n
符号	最小值	典型值	最大值
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1		2.00	
b2		3.00	
С	0.55	0.60	0.75
D	20.80	21.00	21.20
D1		16.55	
D2		1.20	
E	15.60	15.80	16.0
E1		13.30	
E2		5.00	
E3		2.50	
е		5.44	
L	19.42	19.92	20.42
L1		4.13	
Р	3.50	3.60	3.70
P1	-	-	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
Т		10.00	
U		6.20	





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